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**KEITHLEY** INSTRUMENTS

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## **Package 82 Instruction Manual Addendum**

### **INTRODUCTION**

This addendum to the Package 82 Instruction Manual is being provided in order to supply you with the latest information in the least possible time. Please incorporate this information into the manual where indicated.

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Once band bending voltage is known, graphs of  $\psi_s$  vs.  $V_{GS}$ ,  $C_Q$  vs.  $\psi_s$ , and  $C_H$  vs  $\psi_s$  can be generated. Examples are shown in Figures 4-17 through 4-19. Again, CV curves for the device are shown in Figure 4-11.

**$V_{FB}$  and  $\phi_0$  Interpolation**

The program determines flatband voltage,  $V_{FB}$ , by locating the  $V_{GS}$  point where  $C_H$  approximately equals  $C_{FB}$ .  $V_{FB}$  is then interpolated from the closest  $V_{GS}$  values.

A straight line interpolation from the previous or following data points is used, and the interpolated  $V_{FB}$  and  $\phi_0$  points are computed.

**Interface Trap Density vs. Energy from Midgap ( $D_{IT}$  vs  $E_T$ )**

Interface trap density is calculated from  $C_{IT}$  as shown below (Nicollian and Brews 322).

$$C_{IT} = \left( \frac{1}{C_Q} - \frac{1}{C_{OX}} \right)^{-1} - \left( \frac{1}{C_H} - \frac{1}{C_{OX}} \right)^{-1}$$

And:

$$D_{IT} = \frac{(1 \times 10^{-12}) C_{IT}}{Aq}$$

Where:  $C_{IT}$  = interface trap capacitance (pF)  
 $D_{IT}$  = interface trap density ( $\text{cm}^{-2} \text{eV}^{-1}$ )  
 $C_Q$  = quasistatic capacitance (pF)  
 $C_H$  = high-frequency capacitance (pF)

$C_{OX}$  = oxide capacitance (pF)  
 $A$  = gate area ( $\text{cm}^2$ )  
 $q$  = electron charge ( $1.60219 \times 10^{-19} \text{C}$ )  
 $1 \times 10^{-12}$  = units conversion for  $C_{IT}$

The results are stored in the  $D_{IT}$  column of the array as calculated.

Interface trap energy from midgap,  $E_T$ , is computed from  $\psi_s$  offset by bulk potential,  $\phi_B$  as follows:

$$\psi_s - \phi_B - E_T$$

Where:  $\psi_s$  = band bending (V)  
 $E_T$  = interface trap energy from midgap (eV)

And:

$$\phi_B = \frac{kT}{q} \ln \left( \frac{N_x}{n_i} \right)$$

Where:  $\phi_B$  = bulk potential (eV)  
 $kT$  = thermal energy at room temperature ( $4.046 \times 10^{-21} \text{J}$ )  
 $n_i$  = intrinsic carrier concentration in silicon ( $1.45 \times 10^{10} \text{cm}^{-3}$ )  
 $N_x$  =  $N$  at 90%  $w_{MAX}$ , or  $N_A$  or  $N_D$  if entered by the user

A typical example of a  $D_{IT}$  vs.  $E_T$  plot is shown in Figure 4-20.